Elektronische Bauelemente

SMG2314

3.5A, 20V, $R_{DS(ON)}$ 75mΩ

N-Channel Enhancement Mode Power Mos.FET

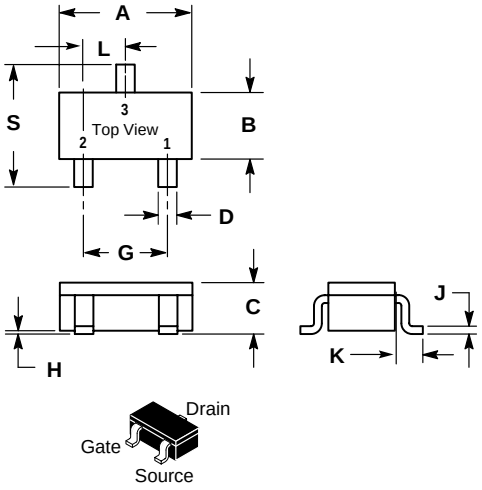
RoHS Compliant Product

Description

The SMG2314 utilized advanced processing techniques to achieve the lowest possible on-resistance, extemely efficient and cost-effectiveness device. The SMG2314 is universally used for all commercial-industrial applications.

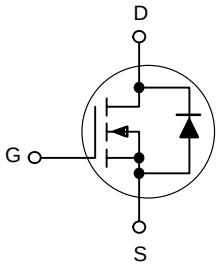
Features

* Low On-Resistance
* Capable Of 2.5V Gate Drive



SC-59		
Dim	**Min**	**Max**
A	2.70	3.10
B	1.40	1.60
C	1.00	1.30
D	0.35	0.50
G	1.70	2.10
H	0.00	0.10
J	0.10	0.26
K	0.20	0.60
L	0.85	1.15
S	2.40	2.80
All Dimension in mm		

Marking : 2314



Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current,[3] V_{GS}@4.5V	I_D@T_A=25°C	3.5	A
Continuous Drain Current,[3] V_{GS}@4.5V	I_D@T_A=70°C	2.8	A
Pulsed Drain Current[1,2]	I_{DM}	10	A
Total Power Dissipation	P_D@T_A=25°C	1.38	W
Linear Derating Factor		0.01	W/°C
Operating Junction and Storage Temperature Range	Tj, Tstg	-55~+150	°C

Thermal Data

Parameter		Symbol	Ratings	Unit
Thermal Resistance Junction-ambient [3]	Max.	Rthj-a	90	°C/W

Electrical Characteristics(Tj=25℃ Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	BV_{DSS}	20	–	–	V	V_{GS}=0V, I_D=250uA
Breakdown Voltage Temp. Coefficient	$\triangle BV_{DS}/\triangle Tj$	–	0.02	–	V/℃	Reference to 25℃, I_D=1mA
Gate Threshold Voltage	$V_{GS(th)}$	0.5	–	1.2	V	V_{DS}=V_{GS}, I_D=250uA
Gate-Source Leakage Current	I_{GSS}	–	–	±100	nA	V_{GS}=±12V
Drain-Source Leakage Current (Tj=25℃)	I_{DSS}	–	–	1	uA	V_{DS}=20V,V_{GS}=0
Drain-Source Leakage Current (Tj=70℃)		–	–	10	uA	V_{DS}=16V,V_{GS}=0
Static Drain-Source On-Resistance	$R_{DS(ON)}$	–	–	75	mΩ	V_{GS}=4.5V, I_D=3.5A
		–	–	125		V_{GS}=2.5V, I_D=1.2A
Total Gate Charge[2]	Qg	–	4	7	nC	I_D=3A V_{DS}=16V V_{GS}=4.5V
Gate-Source Charge	Qgs	–	0.7	–		
Gate-Drain ("Miller") Charge	Qgd	–	2	–		
Turn-on Delay Time[2]	$Td_{(ON)}$	–	6	–	nS	V_{DD}=15V I_D=1A V_{GS}=5V R_G=3.3Ω R_D=15Ω
Rise Time	Tr	–	8	–		
Turn-off Delay Time	$Td_{(Off)}$	–	10	–		
Fall Time	Tf	–	3	–		
Input Capacitance	Ciss	–	230	370	pF	V_{GS}=0V V_{DS}=20V f=1.0MHz
Output Capacitance	Coss	–	55	–		
Reverse Transfer Capacitance	Crss	–	40	–		
Forward Transconductance	Gfs	–	7	–	S	V_{DS}=5V, I_D=3A
Gate Resistance	Rg	–	1.1	1.7	Ω	f=1.0MHz

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Forward On Voltage[2]	V_{DS}	–	–	1.2	V	I_S=1.2A, V_{GS}=0V.
Reverse Recovery Time	Trr	–	16	–	nS	I_S=3A,V_{GS}=0V dI/dt=100A/us
Reverse Recovery Change	Qrr	–	8	–	nC	

Notes: 1.Pulse width limited by Max. junction temperature.
2.Pulse width≦300us, dutycycle≦2%.
3.Surface mounted on FR4 board, t≦10sec.

Elektronische Bauelemente

SMG2314

3.5A, 20V,RDS(ON)75mΩ

N-Channel Enhancement Mode Power Mos.FET

Characteristics Curve

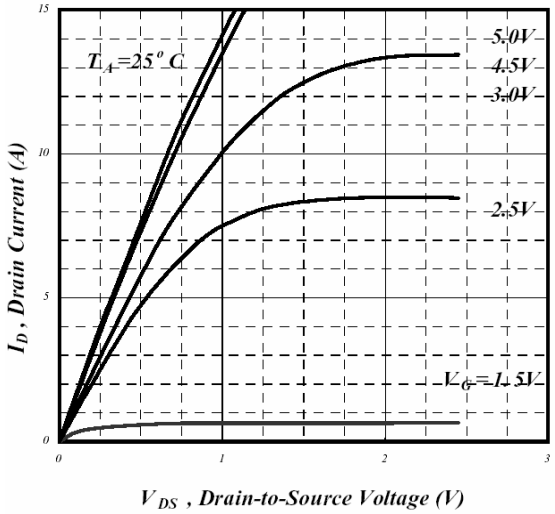


Fig 1. Typical Output Characteristics

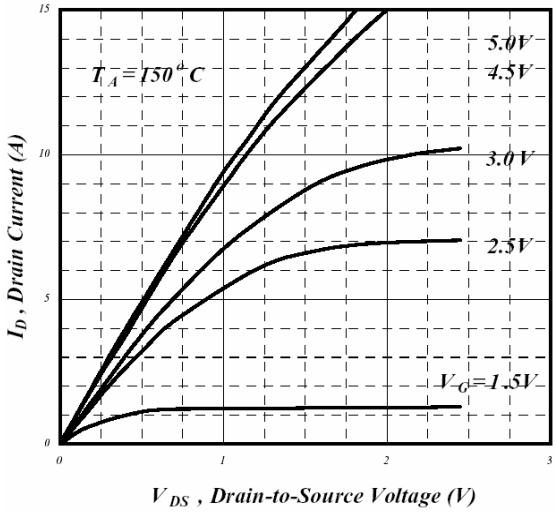


Fig 2. Typical Output Characteristics

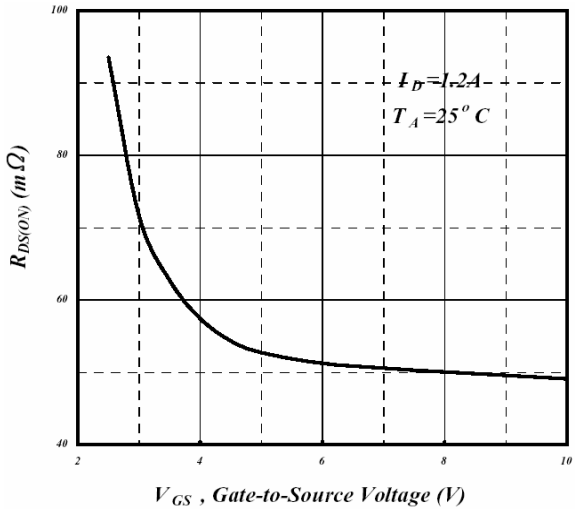


Fig 3. On-Resistance v.s. Gate Voltage

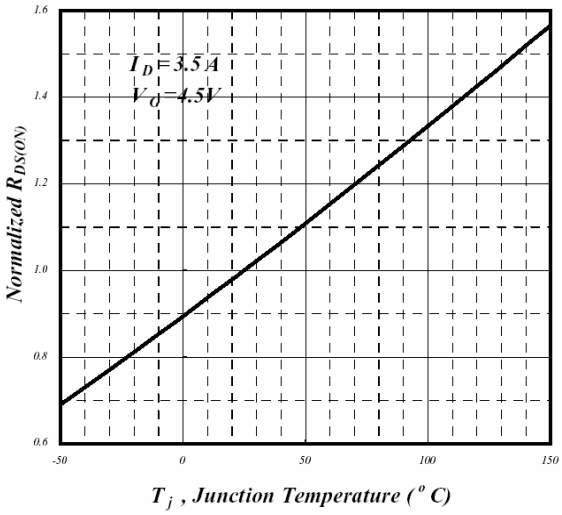


Fig 4. Normalized On-Resistance v.s. Junction Temperature

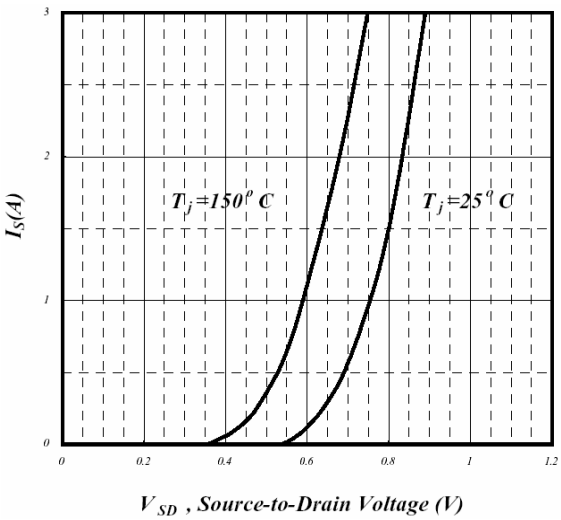


Fig 5. Forward Characteristics of Reverse Diode

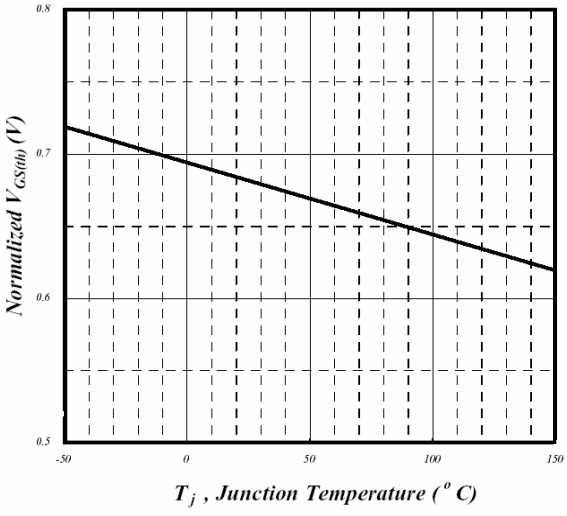


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

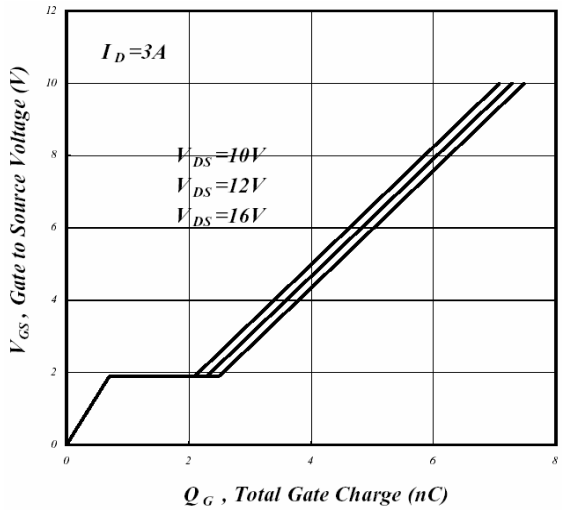


Fig 7. Gate Charge Characteristics

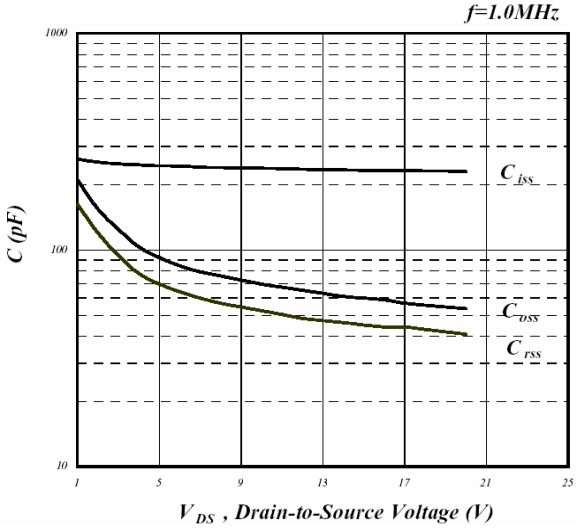


Fig 8. Typical Capacitance Characteristics

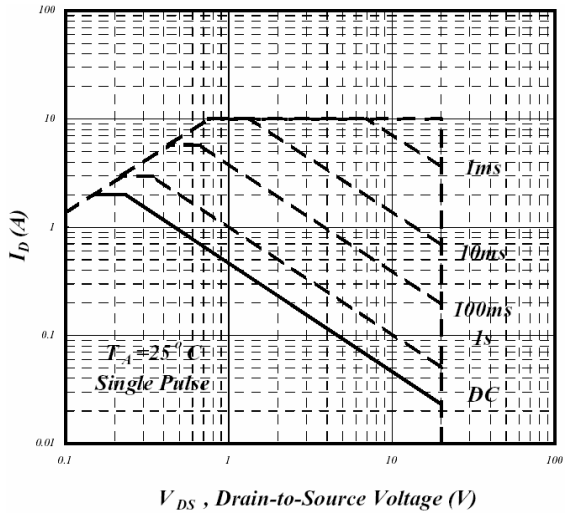


Fig 9. Maximum Safe Operating Area

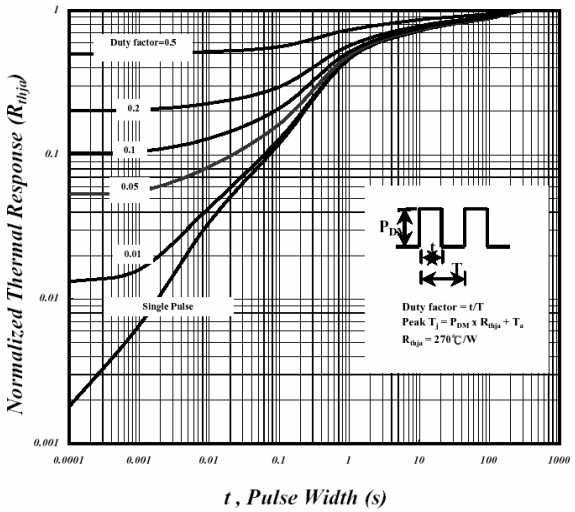


Fig 10. Effective Transient Thermal Impedance

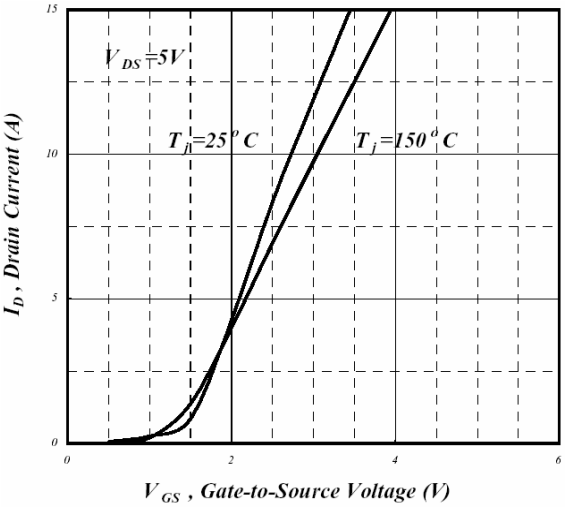


Fig 11. Transfer Characteristics

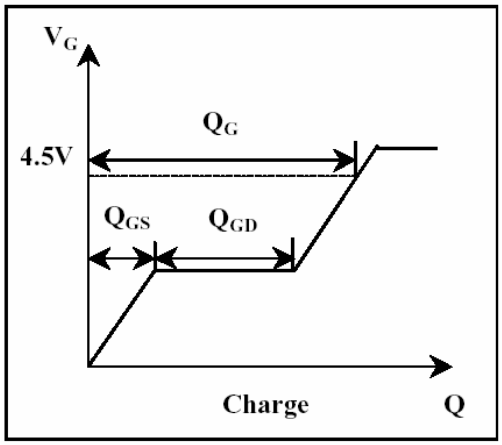


Fig 12. Gate Charge Waveform